

## HUF75617D3-VB Datasheet

### N-Channel 100 V (D-S) MOSFET

#### PRODUCT SUMMARY

$V_{DS}$ (V)	$R_{DS(on)}$ ( $\Omega$ )	$I_D$ (A)
100	0.110 at $V_{GS} = 10$ V	15
	0.115 at $V_{GS} = 6$ V	15

#### FEATURES

- DT-Trench Power MOSFET
- 175 °C Junction Temperature
- 100 %  $R_g$  Tested

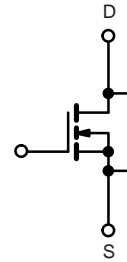


**RoHS**  
COMPLIANT

#### APPLICATIONS

- Primary Side Switch

TO-251



N-Channel MOSFET

#### ABSOLUTE MAXIMUM RATINGS ( $T_C = 25$ °C, unless otherwise noted)

Parameter		Symbol	Limit	Unit
Drain-Source Voltage		$V_{DS}$	100	V
Gate-Source Voltage		$V_{GS}$	$\pm 20$	
Continuous Drain Current ( $T_J = 175$ °C) <sup>b</sup>	$T_C = 25$ °C	$I_D$	15	A
	$T_C = 125$ °C		8.7	
Pulsed Drain Current		$I_{DM}$	45	
Continuous Source Current (Diode Conduction)		$I_S$	15	
Avalanche Current		$I_{AR}$	15	mJ
Repetitive Avalanche Energy (Duty Cycle $\leq 1$ %)	$L = 0.1$ mH	$E_{AR}$	11.3	
Maximum Power Dissipation	$T_C = 25$ °C	$P_D$	61 <sup>b</sup>	W
	$T_A = 25$ °C		2.7 <sup>a</sup>	
Operating Junction and Storage Temperature Range		$T_J, T_{stg}$	- 55 to 175	°C

#### THERMAL RESISTANCE RATINGS

Parameter		Symbol	Typical	Maximum	Unit
Junction-to-Ambient <sup>a</sup>	$t \leq 10$ s	$R_{thJA}$	16	20	°C/W
	Steady State		45	55	
Junction-to-Case		$R_{thJC}$	2	2.4	

Notes:

a. Surface mounted on 1" x 1" FR4 board.

b. See SOA curve for voltage derating.

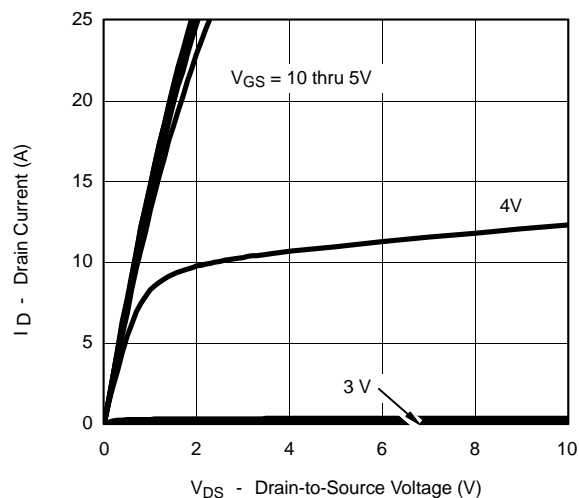
SPECIFICATIONS (T <sub>J</sub> = 25 °C, unless otherwise noted)						
Parameter	Symbol	Test Conditions	Min.	Typ. <sup>a</sup>	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V <sub>DS</sub>	V <sub>GS</sub> = 0 V, I <sub>D</sub> = 250 μA	100			V
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250 μA	1.0		3.0	
Gate-Body Leakage	I <sub>GSS</sub>	V <sub>DS</sub> = 0 V, V <sub>GS</sub> = ± 20 V			± 100	nA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = 100 V, V <sub>GS</sub> = 0 V			1	μA
		V <sub>DS</sub> = 100 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 125 °C			50	
		V <sub>DS</sub> = 100 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 175 °C			250	
On-State Drain Current <sup>b</sup>	I <sub>D(on)</sub>	V <sub>DS</sub> = 5 V, V <sub>GS</sub> = 10 V	15			A
Drain-Source On-State Resistance <sup>b</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 15 A		0.110		Ω
		V <sub>GS</sub> = 10 V, I <sub>D</sub> = 15 A, T <sub>J</sub> = 125 °C		0.170		
		V <sub>GS</sub> = 10 V, I <sub>D</sub> = 15 A, T <sub>J</sub> = 175 °C		0.230		
		V <sub>GS</sub> = 6 V, I <sub>D</sub> = 10 A		0.115		
Forward Transconductance <sup>b</sup>	g <sub>fs</sub>	V <sub>DS</sub> = 15 V, I <sub>D</sub> = 15 A		25		S
Dynamic <sup>a</sup>						
Input Capacitance	C <sub>iss</sub>	V <sub>GS</sub> = 0 V, V <sub>DS</sub> = 25 V, f = 1 MHz		892		pF
Output Capacitance	C <sub>oss</sub>			110		
Reverse Transfer Capacitance	C <sub>rss</sub>			70		
Total Gate Charge <sup>c</sup>	Q <sub>g</sub>	V <sub>DS</sub> = 75 V, V <sub>GS</sub> = 10 V, I <sub>D</sub> = 15 A		20	25	nC
Gate-Source Charge <sup>c</sup>	Q <sub>gs</sub>			5.5		
Gate-Drain Charge <sup>c</sup>	Q <sub>gd</sub>			7		
Gate Resistance	R <sub>g</sub>		1		3.2	Ω
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>	V <sub>DD</sub> = 75 V, R <sub>L</sub> = 5 Ω I <sub>D</sub> ≅ 15 A, V <sub>GEN</sub> = 10 V, R <sub>G</sub> = 2.5 Ω		8	12	ns
Rise Time <sup>c</sup>	t <sub>r</sub>			35	55	
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>			17	25	
Fall Time <sup>c</sup>	t <sub>f</sub>			30	45	
Source-Drain Diode Ratings and Characteristic (T <sub>C</sub> = 25 °C)						
Pulsed Current	I <sub>SM</sub>				45	A
Diode Forward Voltage <sup>b</sup>	V <sub>SD</sub>	I <sub>F</sub> = 15 A, V <sub>GS</sub> = 0 V		0.9	1.5	V
Source-Drain Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> = 15 A, dI/dt = 100 A/μs		55	85	ns

Notes:

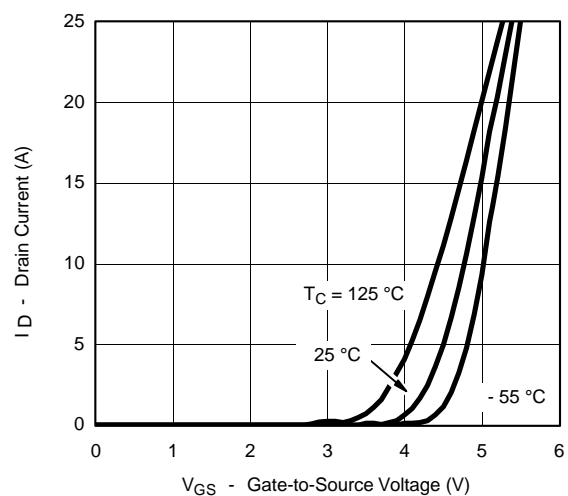
- Guaranteed by design, not subject to production testing.
- Pulse test; pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$ .
- Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

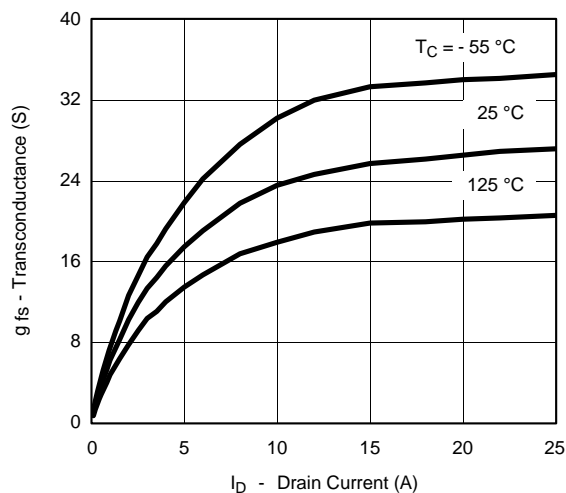
## TYPICAL CHARACTERISTICS (25 °C unless noted)



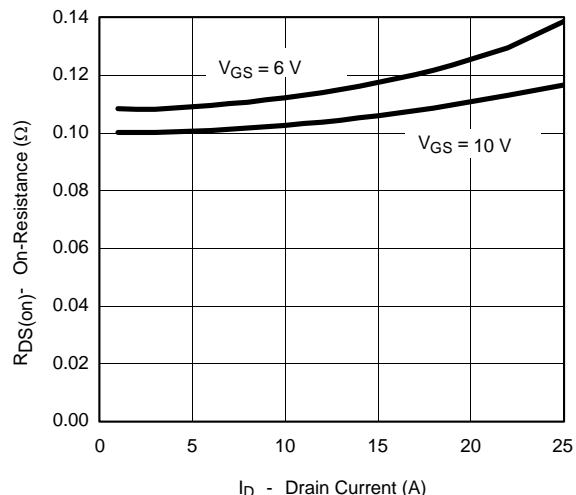
Output Characteristics



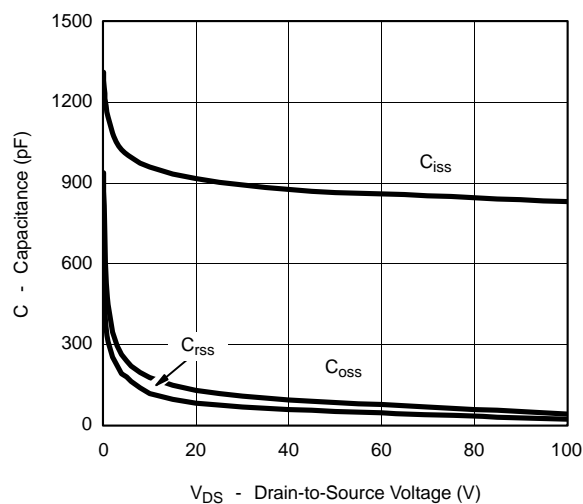
Transfer Characteristics



Transconductance



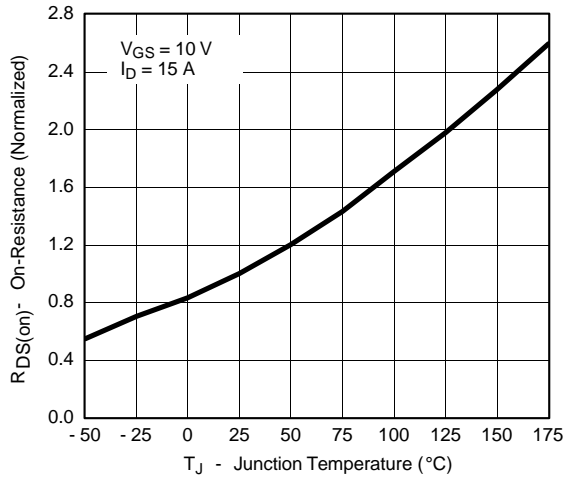
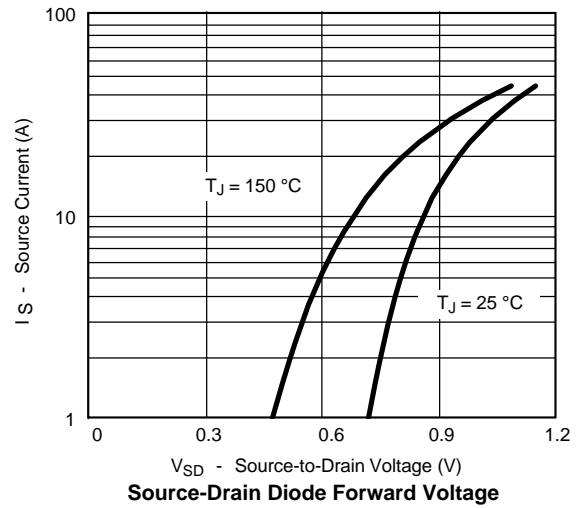
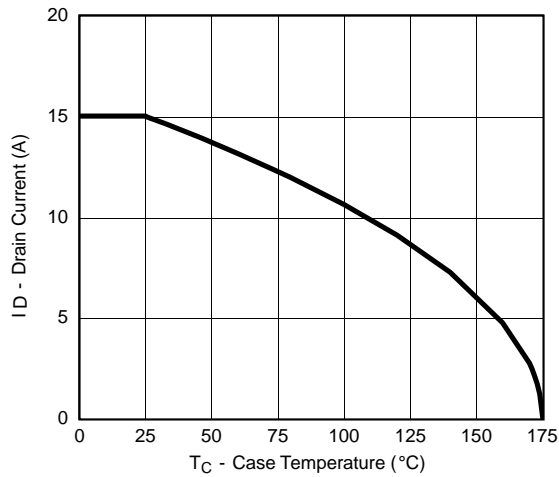
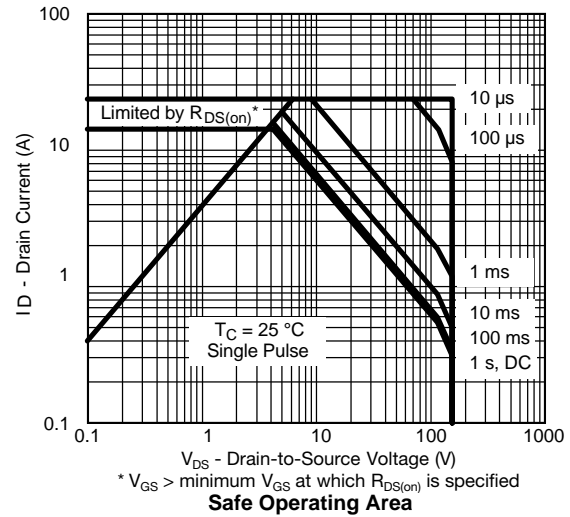
On-Resistance vs. Drain Current



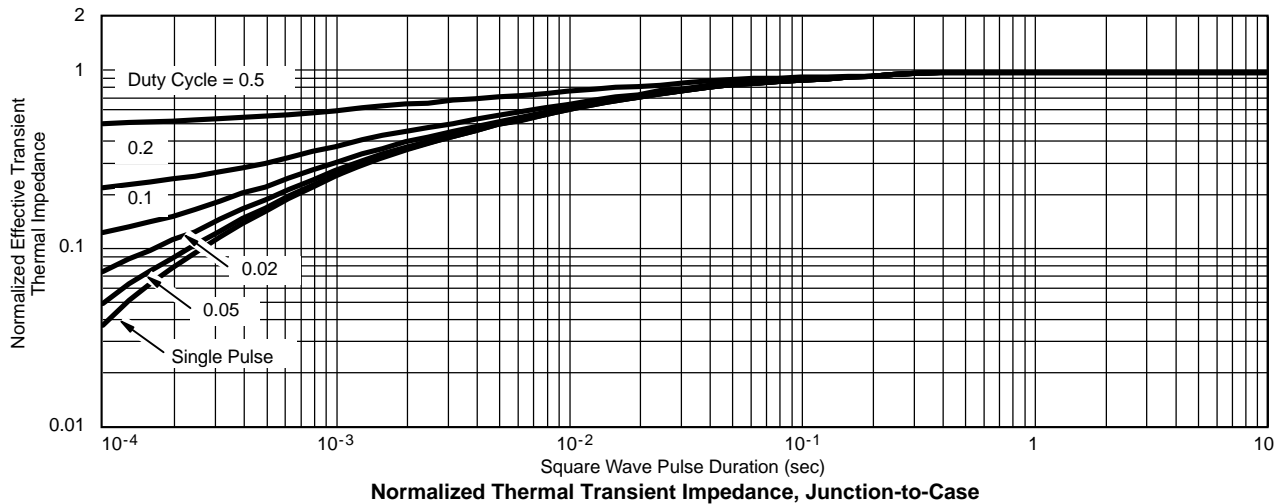
Capacitance



Gate Charge

**TYPICAL CHARACTERISTICS** (25 °C unless noted)

**On-Resistance vs. Junction Temperature**

**Source-Drain Diode Forward Voltage**
**THERMAL RATINGS**

**Maximum Avalanche Drain Current vs. Case Temperature**


\*  $V_{GS} >$  minimum  $V_{GS}$  at which  $R_{DS(on)}$  is specified

**Safe Operating Area**

**Normalized Thermal Transient Impedance, Junction-to-Case**

**TO-251AA (DPAK)**



Note: Dimension L3 is for reference only.

Dim	MILLIMETERS		INCHES	
	Min	Max	Min	Max
<b>A</b>	2.21	2.38	0.087	0.094
<b>A1</b>	0.89	1.14	0.035	0.045
<b>b</b>	0.71	0.89	0.028	0.035
<b>b1</b>	0.76	1.14	0.030	0.045
<b>b2</b>	5.23	5.43	0.206	0.214
<b>c</b>	0.46	0.58	0.018	0.023
<b>c1</b>	0.46	0.58	0.018	0.023
<b>D</b>	5.97	6.22	0.235	0.245
<b>E</b>	6.48	6.73	0.255	0.265
<b>e</b>	2.28 BSC		0.090 BSC	
<b>L</b>	8.89	9.53	0.350	0.375
<b>L1</b>	1.91	2.28	0.075	0.090
<b>L2</b>	0.89	1.27	0.035	0.050
<b>L3</b>	1.15	1.52	0.045	0.060
ECN: S-03946—Rev. E, 09-Jul-01 DWG: 5346				

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